



# 2SK2618LS

N- Channel MOS Silicon FET  
Very High-Speed Switching Applications

## TENTATIVE

### Features and Applications

- Low ON-state resistance.
- Low Qg

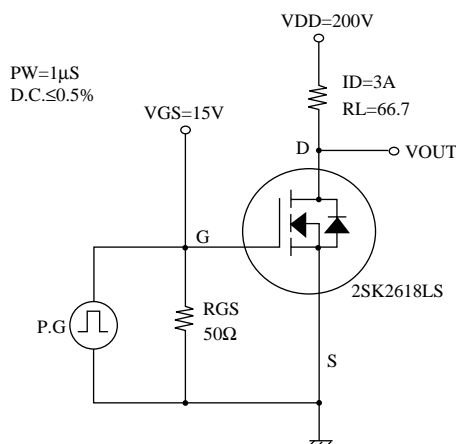
### Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	500	V
Gate to Source Voltage	VGSS	±30	V
Drain Current (DC)	ID	5	A
Drain Current (Pulse)	IDP	20	A
Allowable power Dissipation	PD (Tc=25°C)	30	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

### Electrical Characteristics / Ta=25°C

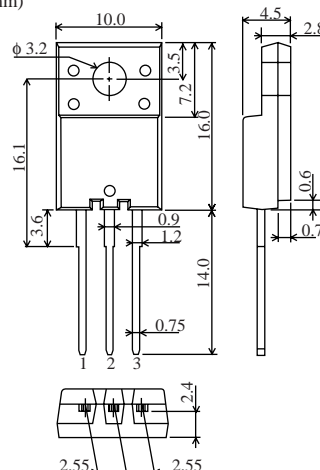
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	500			V
Zero Gate Voltage Drain Current	IDSS	VDS=500V , VGS=0			1.0	mA
Gate to Source Leakage Current	IGSS	VGS=±30V , VDS=0			±100	nA
Cutoff Voltage	VGS(off)	VDS=10V , ID=1mA	3.5		5.5	V
Forward Transfer Admittance	yfs	VDS=10V , ID=3A	1.5	3.0		S
Static Drain to Source on State Resistance	RDS(on)	ID=3A , VGS=15V		0.95	1.25	Ω
Input Capacitance	Ciss	VDS=20V , f=1MHz		700		pF
Output Capacitance	Coss	VDS=20V , f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	VDS=20V , f=1MHz		120		pF
Total Gate Charge	Qg	VDS=200V , ID=5A GS=10V		20		nC
Turn-ON Delay Time	td(on)	See Specified Test Circuit		20		ns
Rise Time	tr			20		ns
Turn-off Delay Time	td(off)			50		ns
Fall Time	tf			25		ns
Diode Forward Voltage	VSD	IS =5A , VGS = 0			1.2	V

### Switching Time Test Circuit



### Case Outline

TO-220F(LS)  
(unit:mm)



Specifications and information herein are subject to change without notice.

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